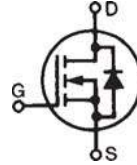


**HiPerRF™**  
**Power MOSFETs**  
**F-Class: MegaHertz Switching**

**IXFK24N100F**  
**IXFX24N100F**

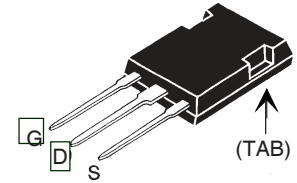
**V<sub>DSS</sub> = 1000V**  
**I<sub>D25</sub> = 24A**  
**R<sub>DS(on)</sub> ≤ 390mΩ**  
**t<sub>rr</sub> ≤ 250ns**

N-Channel Enhancement Mode  
 Avalanche Rated, Low Q<sub>g</sub>, Low  
 Intrinsic R<sub>g</sub>, High dV/dt, Low t<sub>rr</sub>

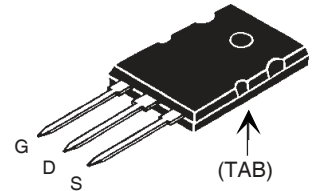


Symbol	Test Conditions	Maximum Ratings	
V <sub>DSS</sub>	T <sub>J</sub> = 25°C to 150°C	1000	V
V <sub>DGR</sub>	T <sub>J</sub> = 25°C to 150°C, R <sub>GS</sub> = 1MΩ	1000	V
V <sub>GSS</sub>	Continuous	± 20	V
V <sub>GSM</sub>	Transient	± 30	V
I <sub>D25</sub>	T <sub>C</sub> = 25°C	24	A
I <sub>DM</sub>	T <sub>C</sub> = 25°C, Pulse Width Limited by T <sub>JM</sub>	96	A
I <sub>A</sub>	T <sub>C</sub> = 25°C	24	A
E <sub>AS</sub>	T <sub>C</sub> = 25°C	3	J
dV/dt	I <sub>S</sub> ≤ I <sub>DM</sub> , di/dt ≤ 100A/μs, V <sub>DD</sub> ≤ V <sub>DSS</sub> T <sub>J</sub> ≤ 150°C, R <sub>G</sub> = 2Ω	15	V/ns
P <sub>D</sub>	T <sub>C</sub> = 25°C	560	W
T <sub>J</sub>		-55 ... +150	°C
T <sub>JM</sub>		150	°C
T <sub>stg</sub>		-55 ... +150	°C
T <sub>L</sub>	1.6mm (0.062 in.) from Case for 10s	300	°C
T <sub>SOLD</sub>	Plastic Body for 10s	260	°C
M <sub>d</sub>	Mounting Torque (TO-264)	1.13/10	Nm/lb.in.
F <sub>C</sub>	Mounting Force (PLUS247)	20..120 / 4.5..27	N/lb.
Weight	TO-264	10	g
	PLUS247	6	g

**PLUS 247™ (IXFX)**



**TO-264 AA (IXFK)**



G = Gate                      D = Drain  
 S = Source                    TAB = Drain

**Features**

- RF capable MOSFETs
- Double metal process for low gate resistive
- Avalanche rated
- Low package inductance
- Fast intrinsic rectifier

**Applications**

- DC-DC converters
- Switched-mode and resonant-mode power supplies, >500kHz switching
- DC choppers
- 13.5 MHz industrial applications
- Pulse generation
- Laser drivers
- RF amplifiers

**Advantages**

- PLUS 247™ package for clip or spring mounting
- Space savings
- High power density

Symbol	Test Conditions (T <sub>J</sub> = 25°C Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA	1000		V
V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 8mA	3.0		5.5 V
I <sub>GSS</sub>	V <sub>GS</sub> = ± 20V, V <sub>DS</sub> = 0V			± 200 nA
I <sub>DSS</sub>	V <sub>DS</sub> = V <sub>DSS</sub> , V <sub>GS</sub> = 0V T <sub>J</sub> = 125°C			100 μA 3 mA
R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.5 • I <sub>D25</sub> , Note 1			390 mΩ

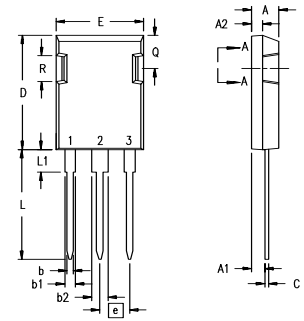
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{V}, I_D = 0.5 \cdot I_{D25}$ , Note 1	16	24	S
$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		6600	pF
$C_{oss}$			760	pF
$C_{rss}$			230	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\Omega$ (External)		22	ns
$t_r$			18	ns
$t_{d(off)}$			52	ns
$t_f$			11	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		195	nC
$Q_{gs}$			40	nC
$Q_{gd}$			100	nC
$R_{thJC}$			0.21	$^\circ\text{C/W}$
$R_{thCK}$		0.15		$^\circ\text{C/W}$

Source-Drain Diode	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			24 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			96 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 24\text{A}, -di/dt = 100\text{A}/\mu\text{s}$			250 ns
$Q_{RM}$			1.4	$\mu\text{C}$
$I_{RM}$	$V_R = 100\text{V}, V_{GS} = 0\text{V}$		10	A

Note: 1. Pulse test,  $t \leq 300 \mu\text{s}$ , duty cycle  $d \leq 2\%$

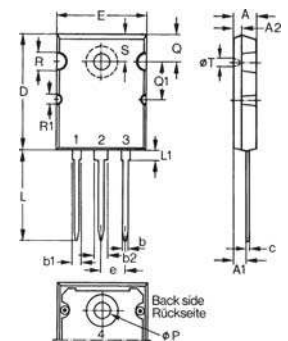
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**PLUS247™ Outline**


Terminals: 1 - Gate  
2 - Drain (Collector)  
3 - Source (Emitter)  
4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A <sub>1</sub>	2.29	2.54	.090	.100
A <sub>2</sub>	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b <sub>1</sub>	1.91	2.13	.075	.084
b <sub>2</sub>	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

**TO-264 AA Outline**


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A <sub>1</sub>	2.54	2.89	.100	.114
A <sub>2</sub>	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b <sub>1</sub>	2.39	2.69	.094	.106
b <sub>2</sub>	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072